

## P-Channel 100V MOSFET

### E38P100KC

$V_{DS}$ (V)	$R_{DS(on),max}$ (m $\Omega$ )	$I_D$ (A)
-100	50@ $V_{GS} = -10V$	-38

### Features

- Trench MOS technology
- Low  $R_{DS(on)}$ , Low  $Q_g$
- Excellent Gate Charge x  $R_{DS(ON)}$  Product (FOM)

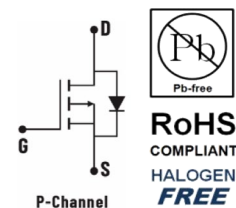
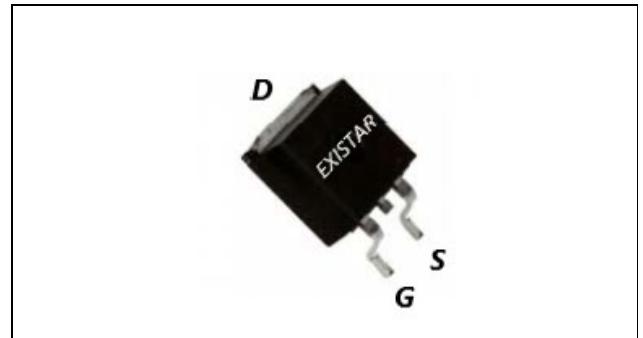
### Applications

- Fast switching

### Package and ordering information

Ordering code	Package	Device code
E38P100KC	TO252	---

### TO252



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		$V_{DS}$	-100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous drain current	$TC=25^\circ\text{C}$	$I_D$	-38	A
	$TC=100^\circ\text{C}$	$I_D$	-18	A
Drain Current – Pulsed		$I_{DM}$	-120	A
Maximum Power Dissipation		$P_D$	104	W
Single pulse avalanche energy		$E_{AS}$	285	mJ
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance junction-case	$R_{\theta JC}$		1.2	$^\circ\text{C} / \text{W}$
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		62	$^\circ\text{C} / \text{W}$

**Electrical Characteristics(TJ=25 °C unless otherwise noted)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
STATICPARAMETERS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V,I <sub>D</sub> =-250μA	-100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-100V,V <sub>GS</sub> =0V			-1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μ A	-1.5	-1.9	-2.5	V
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A		35	50	mΩ
		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-5A		42	60	mΩ
gfs	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-5A		23		S
DYNAMICPARAMETERS						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-25V,V <sub>GS</sub> =0V, F=1.0MHz		4387		pF
C <sub>oss</sub>	Output Capacitance			228		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			150		pF
SWITCHINGPARAMETERS						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-50V,I <sub>D</sub> =-15A, V <sub>GS</sub> =-10V, R <sub>G</sub> =9.1Ω		10		nS
t <sub>r</sub>	Turn-on Rise Time			41		nS
t <sub>d(off)</sub>	Turn-Off Delay Time			245		nS
t <sub>f</sub>	Turn-Off Fall Time			87		nS
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-50V,I <sub>D</sub> =-15A, V <sub>GS</sub> =0到-10V		81		nC
Q <sub>gs</sub>	Gate-Source Charge			18		nC
Q <sub>gd</sub>	Gate-Drain Charge			14.5		nC
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V,I <sub>SD</sub> =-1A			-1.4	V

## Electrical Characteristics Diagrams

图 1. 输出特性

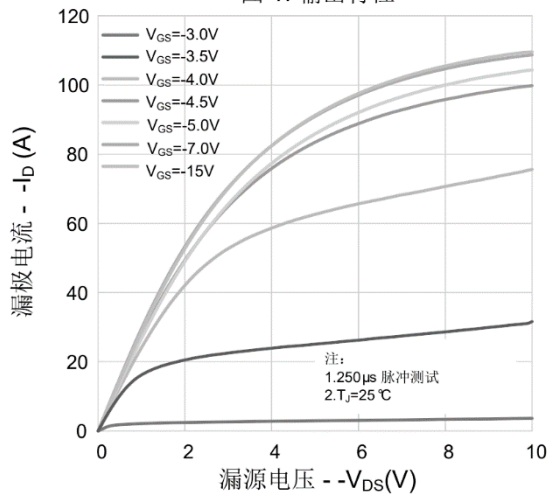


图 2. 传输特性

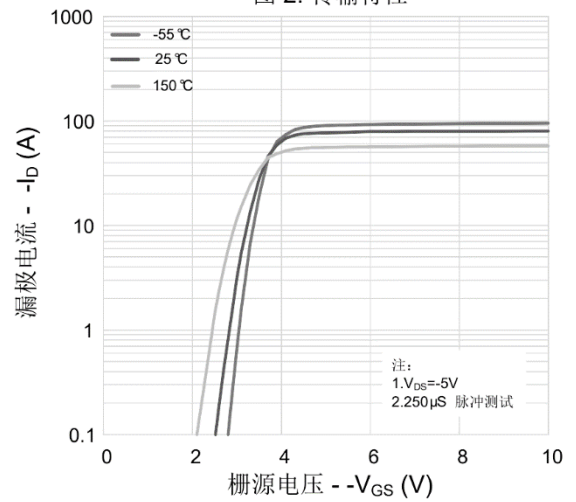


图 3. 导通电阻 vs. 漏极电流

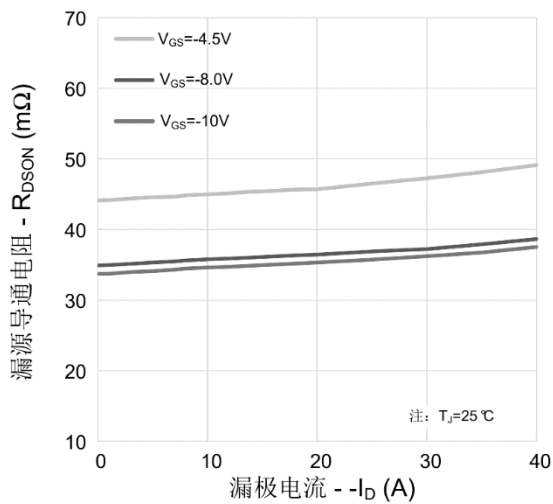


图 4. 导通电阻 vs. 栅源电压

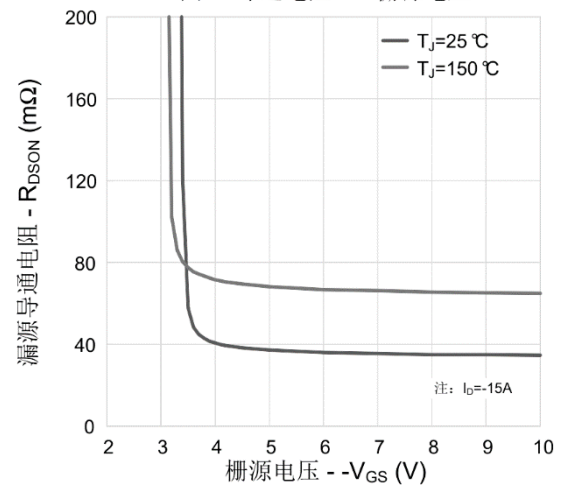


图 5. 开启电压 vs. 温度特性

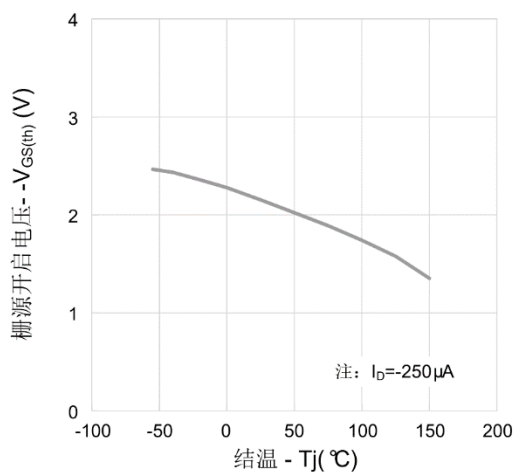


图6. 体二极管正向压降 vs. 源极电流和温度

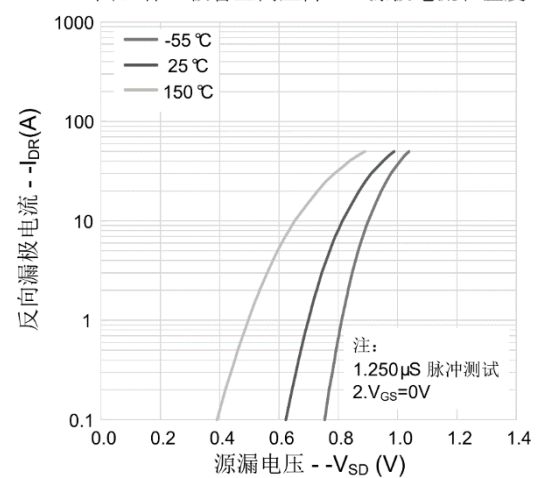


图7. 电容特性

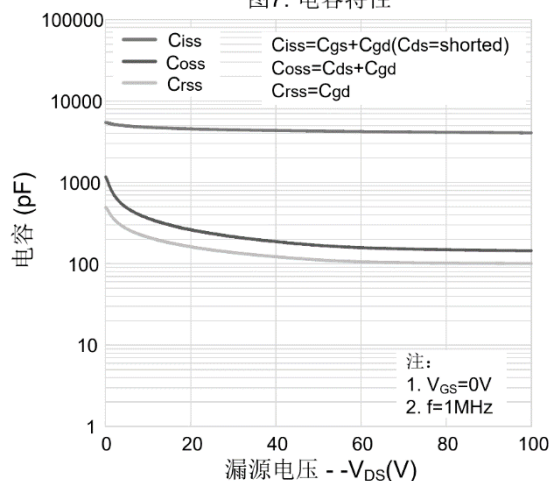


图 8. 电荷量特性

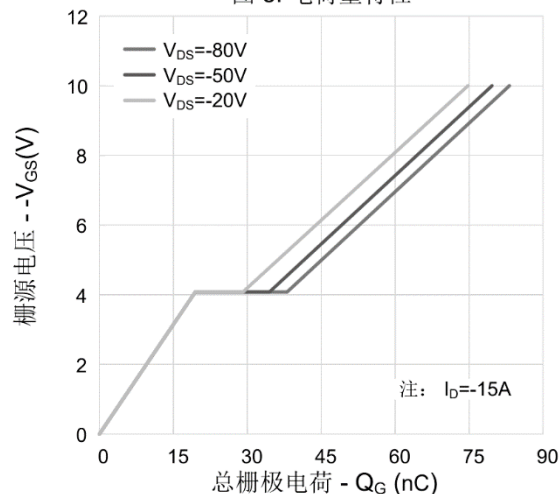


图 9. 击穿电压 vs. 温度特性

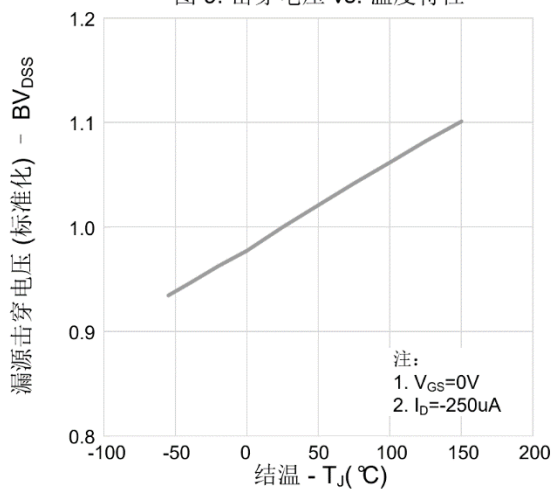


图 10. 导通电阻 vs. 温度特性

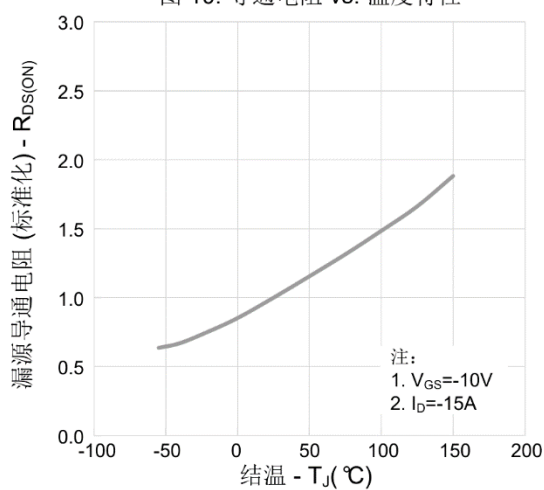


图 11. 最大安全工作区域

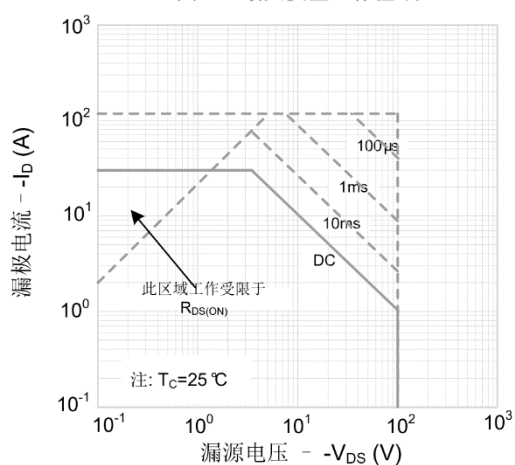
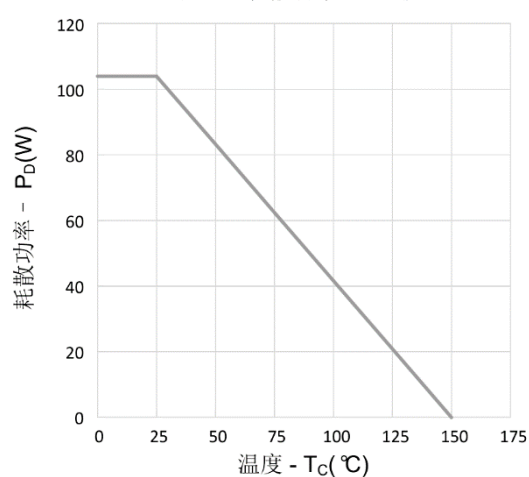
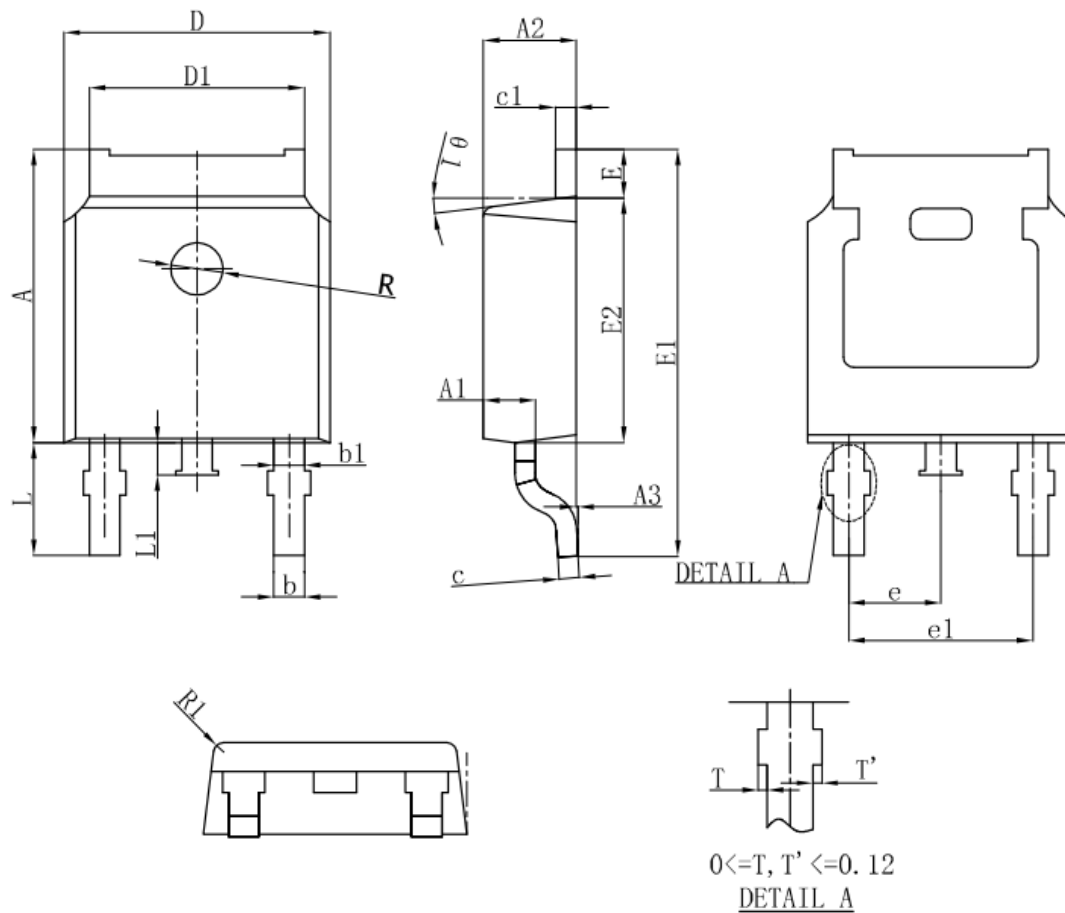


图 12. 耗散功率 vs. 温度



## Package Outline Dimensions



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	7.050	7.100	7.150
A1	0.960	1.010	1.060
A2	2.250	2.300	2.350
A3	0.000	0.050	0.100
b	0.760REF.		
b1	1.000REF.		
c	0.508REF.		
c1	0.508REF.		
D	6.550	6.600	6.650
D1	5.220	5.320	5.420
E	0.950	1.000	1.050
E1	9.700	9.900	10.100
E2	6.050	6.100	6.150
e	2.286BSC		
e1	4.572REF.		
L	2.650	2.800	2.950
L1	0.700	0.800	0.900
$\theta$	7° REF.		
R	0.250REF.		

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